

ABSTRACT OF THE DISCLOSURE

A low-k dielectric film is formed on an entire surface of a substrate having a pad region and a circuit region. A resist pattern
5 is formed on the low-k dielectric film, and an opening is formed in the low-k dielectric film of the pad region using the resist pattern as a mask. A silicon oxide film having strength higher than the low-k dielectric film is formed in the opening using liquid-phase deposition method. Wirings are formed in the silicon oxide film of the pad region
10 and in the low-k dielectric film of the circuit region using damascene method.